

	Hits	Search Text	DBs
1	566	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2))))	USPAT; US-PGPUB
2	83	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))) and (((semiconductor silicon adj nitride polycrystalline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number))))	USPAT; US-PGPUB
3	25	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))) and (((semiconductor silicon adj nitride polycrystalline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number)))) and actual\$3	USPAT; US-PGPUB
4	6	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))) and (((semiconductor silicon adj nitride polycrystalline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number)))) and (odd\$1number (odd near2 number))	USPAT; US-PGPUB
5	3	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))) and (layers with (odd\$1number (odd near2 number)))	USPAT; US-PGPUB
6	1	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))) and (((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number))))	USPAT; US-PGPUB
7	35	freestanding adj membrane	USPAT; US-PGPUB
8	50	((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number)))	USPAT; US-PGPUB
9	11	((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number))) and ((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film))	USPAT; US-PGPUB
10	14	((deformable flexible freestanding) near2 (film membrane pellicle (thin adj film) thin\$1film)) and (layers with (odd\$1number (odd near2 number)))	USPAT; US-PGPUB
11	75	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2))))	EPO; JPO; DERWENT
12	2	(((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film)) same (electrostatic electro\$1magnetic)) and ((optic\$2 opto\$1electronic mem mems photonic) ((dielectric semiconductor) with (layer\$2 multi\$1layer\$2)))) and (((semiconductor silicon adj nitride polycrystalline adj silicon) near2 layer\$1) (layers with symmet\$5) (layers with (odd\$1number (odd near2 number))))	EPO; JPO; DERWENT
13	2	freestanding adj membrane	EPO; JPO; DERWENT
14	18	((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number)))	EPO; JPO; DERWENT
15	4	((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number))) and ((deformable flexible freestanding multi\$1layer\$2) near2 (film membrane pellicle (thin adj film) thin\$1film))	EPO; JPO; DERWENT
16	1	("20030045036").PN.	USPAT; US-PGPUB
17	13	((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) near2 layer\$1) same ((layers multi\$1layers) with (odd\$1number (odd near2 number))) same (mirror\$ micro\$1mirror\$1))	USPAT; US-PGPUB
18	15	(((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) near2 layer\$1) with (odd\$1number (odd near2 number))) and 359/(290-298).ccls.	USPAT; US-PGPUB
19	153	((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) with mirror) and ((359/290).ccls.(359/291).ccls. (359/292).ccls. (359/293).ccls. (359/294).ccls. (359/295).ccls. (359/298).ccls.)	USPAT; US-PGPUB
20	77	((semiconductor dielectric silicon adj nitride polycrystalline adj silicon) with mirror with layer\$1) and ((359/290).ccls.(359/291).ccls. (359/292).ccls. (359/293).ccls. (359/294).ccls. (359/295).ccls. (359/298).ccls.)	USPAT; US-PGPUB
21	7	intpax.as.	USPAT; US-PGPUB
22	26	(elm adj technology).as.	USPAT; US-PGPUB
23	5	("4756602"   "5023944"   "5144498"   "5583683"   "5719989").PN.	USPAT
24	5	("4756602"   "5023944"   "5144498"   "5583683"   "5719989").PN.	USPAT

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	Hits	Search Text	DBs
25	5	("4756602"   "5023944"   "5144498"   "5583683"   "5719989").PN.	USPAT
26	4	("5144498"   "5212584"   "5410431"   "5583683").PN.	USPAT
27	6	5999322.URPN.	USPAT
28	591	(359/291).CCLS.	USPAT; US-PGPUB
29	199	(359/321).CCLS.	USPAT; US-PGPUB
30	454	(359/580).CCLS.	USPAT; US-PGPUB
31	372	(359/586).CCLS.	USPAT; US-PGPUB
32	241	(359/588).CCLS.	USPAT; US-PGPUB
33	714	(216/13).CCLS.	USPAT; US-PGPUB
34	560	(216/24).CCLS.	USPAT; US-PGPUB
35	402	(438/29).CCLS.	USPAT; US-PGPUB

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	1	2	C	3	Document	Title	Current OR
1	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US H001886 H	Optical thin-film cavities for transducing visible radiation to infrared radiation	385/119
2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6558868 B2	Method of fabricating a high aspect ratio microstructure	430/259
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6556338 B2	MEMS based variable optical attenuator (MBVOA)	359/298
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6509998 B2	Tunable multi-channel optical attenuator (TMCOA)	359/245
5	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6373632 B1	Tunable Fabry-Perot filter	359/578
6	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6331257 B1	Fabrication of broadband surface-micromachined micro-electro-mechanical switches for microwave and millimeter-wave applications	216/13
7	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6046659 A	Design and fabrication of broadband surface-micromachined micro-electro-mechanical switches for microwave and millimeter-wave applications	333/262
8	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5999322 A	Multilayer thin film bandpass filter	359/589
9	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030045036 A1	Robust multi-layered thin-film membrane for micro-electromechanical systems (MEMS) photonic devices	438/149
10	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030016436 A1	Fabry-Perot cavity manufactured with bulk micro-machining process applied on supporting substrate	359/321
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030012231 A1	Microelectromechanically tunable, confocal, vertical cavity surface emitting laser and fabry-perot filter	372/20
12	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020191929 A1	Omnidirectional multilayer device for enhanced optical waveguiding	385/127
13	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020150377 A1	Method for attenuation of optical signals using reflective membrane device	385/140
14	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020122252 A1	Optical bodies made with a birefringent polymer	359/498
15	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020110948 A1	Defined sacrificial region via ion implantation for micro-opto-electro-mechanical system (MOEMS) applications	438/57
16	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020080504 A1	Triple electrode MOEMS tunable filter and fabrication process therefor	359/872
17	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020080465 A1	MEMS based variable optical attenuator (MBVOA)	359/291
18	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020071463 A1	Surface-emitting semiconductor laser	372/45
19	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020054416 A1	Tunable multi-channel optical attenuator (TMCOA)	359/245
20	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	JP 2000232236 A	NITRIDE SEMICONDUCTOR ELEMENT	

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